

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Constantin Bulucea and Rebecca Rossen
 Assignee: Siliconix incorporated
 Title: TRENCH DMOS POWER TRANSISTOR WITH FIELD-SHAPING
 BODY PROFILE AND THREE-DIMENSIONAL GEOMETRY
 Serial No.: Unknown Filed: Herewith
 Examiner: J. Carroll Group Art Unit: 2508
 Attorney Docket No.: M-799-4C US

San Jose, California
 May 5, 1997

COMMISSIONER OF PATENTS AND TRADEMARKS
 Washington, D. C. 20231

PRELIMINARY AMENDMENT

Sir:

In response to the Final Office Action of January 8, 1997 in the parent application, serial no. 08/453,285, filed May 30, 1995, Applicants amend the above-referenced patent application as follows:

IN THE CLAIMS

Please cancel Claim 24.

In Claim 58, at line 1, please delete "54" and substitute
 --55--...

Please amend Claims 17, 30, 32 and 54 as follows:

17. (Twice amended) A trench DMOS transistor cell, comprising:

a substrate of a first conductivity type, said substrate having a surface;

an epitaxial layer of said first conductivity type formed on said surface of said substrate, said epitaxial layer having a top surface and a bottom surface, said epitaxial layer having a substantially uniform initial dopant concentration at formation;

a body region of a second conductivity type formed in said epitaxial layer, said body region extending, as

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